AMENDMENTS TO THE SPECIFICATION

Please replace paragraph [0023] with the following amended paragraph:

Fig.9 to Fig.14 are schematic diagrams of a method of forming a liquid crystal on silicon (LCOS) display pixel cell according to the present invention.

Fig.15 is a is a cross-sectional diagram along line B-B' in Fig.8.

Please replace paragraph [0026] with the following amended paragraph:

Please refer to Fig.9 to Fig.1[4]5 of schematic diagram of forming the present invention liquid crystal on silicon (LCOS) display pixel cell 246. Fig.9 to Fig.14 are cross-sectional diagrams along line A-A' in Fig.8. Fig.15 is a cross-sectional diagram along line B-B' in Fig.8. As shown in Fig.9, the present invention LCOS display pixel cell 246 is made on a semiconductor wafer 200. The semiconductor wafer 200 comprises a P-type silicon substrate 202. A plurality of isolator 204 are disposed on the surface of the P-type silicon substrate 202 for defining the active area 104 for each device. The isolator 204 is usually a field oxide layer formed by a local oxidation (LOCOS) or a shallow trench isolation (STI).

Please replace paragraph [0029] with the following

amended paragraph:

In Fig.9 to Fig.14, all of the cross-sectional diagrams are drawn along line A-A' in Fig.8. In order to illustrate the relative sites for sources, drains, and gates more clearly, Fig.15 is drawn along line B-B' in Fig.8 such that at least one complete transistor 106 is shown in a cross section. Thereafter, as shown in Fig.11 and Fig.15, a photoresist layer (not shown) is utilized and an ion and an ion implantation process is performed to form a source/drain (S/D) 215, 216 of the transistor in the P-type substrate 202 at either side of the transistor gate 214. After that, as shown in Fig.11, a first dielectric layer 218 is formed on transistor gate 214 and the isolator 204. The first dielectric layer 218 is formed of silicon dioxide by a chemical vapor deposition (CVD) process, a plasma enhanced chemical vapor deposition (PECVD) process, or a process utilizing tetra-ethyl-ortho-silicate (TEOS). Alternatively, the first dielectric layer 218 sometimes is formed with an additional silicon nitride (Si_3N_4) linear underneath by a plasma enhanced chemical vapor deposition (PECVD) process.